# **TOSHIBA MOS MEMORY PRODUCTS**

8,192 WORD × 8 BIT UV ERASABLE AND TMM2764AD-15, TMM2764AD-150 ELECTRICALLY PROGRAMMABLE READ ONLY IMEMORY TMM2764AD-20, TMM2764AD-200

#### DESCRIPTION

The TMM2764 AD is a 8192 word ×8 bit ultraviolet light erasable and electrically programmable read only memory. For read operation, the TMM2764 AD's access time is 150ns/200ns, and the TMM2764 AD operates from a single 5-volt power supply and has a low power standby mode which reduces the power dissipation without increasing access time.

The standby mode is achieved by applying a TTL-high level signal to the CE input.

For program operation, the programming is achieved by using the high speed programming mode.

The TMM2764AD is fabricated with the N-channel silicon double layer gate MOS technology.

#### **FEATURES**

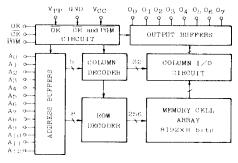
	- 15	-20	150	200	
Vcc.	5V±	5%	5V±10%		
tacc	150ns	200ns	150rs	200ns	
Icc2		)mA	120	mA	
Icci	30	mA	351		

- Full static operation
- High speed programming mode
- Single location programming
- Three state outputs
- Inputs and outputs TTL compatible
- Pin compatible with i2764 A

#### PIN CONNECTION (TOP VIEW)

VPPE		28 <b>b</b>	$v_{\rm CC}$
A 12 C	2	27	PGM
A7 D			N.C.
A <sub>6</sub> C	4	25 🕽	Ag
A <sub>5</sub> C	5		AΘ
A <sub>4</sub>	6		$A_{11}$
A3 C	7	220	
A <sub>2</sub> C	B	210	$A_{10}$
Ald	9	201	
A <sub>O</sub> C	10	190	
00 0	1.1		06
01	12	17	05
02 🗅	13	16	04
GND C	14	15]	$o_3$

#### **BLOCK DIAGRAM**



#### **PIN NAMES**

$A_0 \sim A_{12}$	Address Inputs
On~O/	Outputs (Inputs)
CE	Chip Enable Input
30	Output Enable Input
PGM	Program Control Input
N. C.	No Connection
Vpp	Program Supply Voltage
Vcc	Power Supply Voltage (+5V)
GND	Ground

#### MODE SELECTION

PIN MODE	PGM (27)		OE (22)			0 <sub>0</sub> ~0 <sub>7</sub> (11~13, 15~19)	POWER
Read	Н	Į.	L			Data Out	
Output Deselect	*	*	Н	5V	5V	High Impedance	Active
Standby	*	Н	*			High Impedance	Standby
Program	L	L	*			Data In	
Program	*	H	*	12.5V	6V	High Impedance	A
Inhibit	Н	۱.	H	12.50	00	High Impedance	Active
Program Verify	Н	L.	1			Data Out	

Note: \*; H or L

## MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT	
Vcc	Power Supply Voltage	-0.6-7.0		
VPP	Program Supply Voltage	-0.6~14.0	<u>`</u>	
VIN	Input Voltage	0.6~7.0	V	
Vizo	Input/Output Voltage	-0.6~7.0	<del>-</del>	
Po	Power Dissipation	1.5	<del>-</del>	
TSOLDER	Soldering Temperature · Time	260 · 10	°C·sec	
T <sub>STG</sub>	Storage Temperature	-65~125		
Topr.	Operating Temperature	0~70	°C	

## **READ OPERATION**

## D. C. AND A.C. RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	TMM2764AD-15/20	TMM2764AD-150/200
Та	Operating Temperature	0~70°C	0~70°C
Vcc	Vcc Power Supply Voltage	5V±5%	5V±10%
Vpp	VPP Power Supply Voltage	2.0~V <sub>CC</sub> +0.6V	2.0~V <sub>CC</sub> +0.6V

## D. C. AND OPERATING CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIC	N	MIN.	TYP.	MAX.	UNIT
ILI	Input Current	V <sub>IN</sub> =0~V <sub>CC</sub>			_	±10	μА
lto	Output Leakage Current	Vout=0.4~Vcc			_	±10	μА
lcc1	Supply Current (Standby)	GE 14	-15/20	†		30	<u> </u>
1CC1	Supply Current (Standby)	CE = V <sub>IH</sub>	-150/200		_	35	mA
Icc2	Supply Current (Active)	CF = VII	-15/20			- 100	
1002		CE≡VII	-150/200		_	120	mA
ViH	Input High Voltage			2.0		Vcc + 1.0	V
Vit	Input Low Voltage			-0.3	_	0.8	V
Vон	Output High Voltage	$I_{OH} = -400 \mu A$		2.4			V
Vol	Output Low Voltage	lot = 2.1mA				0.4	V
I <sub>PP1</sub>	V <sub>PP</sub> Current	V <sub>PP</sub> =0~V <sub>CC</sub> +0.6				±10	μA

#### A. C. CHARACTERISTICS

SYMBOL	DADAMETED	TMM2764	AD-15/150	TMM2764		
	PARAMETER	MIN.	MAX.	MIN.	MAX.	UNIT
tacc	Address Access Time		150		200	ns
tor	CE to Output Valid		150		200	ns
tor	OE to Output Valid		73	_	70	ns
tegM	PGM to Output Valid		70		70	ns
tori	CE to Output in High-Z	0	60	0	60	ns
tor 2	OE to Output in High-Z	0	60	0	60	ns
tora :	PGM to Output in High-Z	0	60	0	60	ns
ton	Output Data Hold Time	0		0		ns

## A. C. TEST CONDITIONS

• Output Load : 1 TTL Gate and  $C_L = 100 pF$ 

Input Pulse Rise and Fall Times
 Input Pulse Levels
 10ns Max.
 0.45V to 2.4V

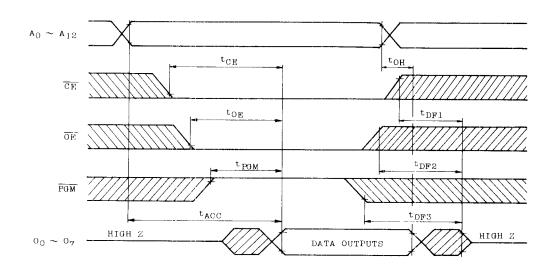
• Timing Measurement Reference Level : Inputs 0.8V and 2.0V, Outputs 0.8V and 2.0V

### **CAPACITANCE** \* (Ta = 25°C, f = 1MHz)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UŇIT
Cin	Input Capacitance	V <sub>IN</sub> = OV	_	4	6	pF
Соьт	Output Capacitance	V <sub>OU1</sub> = OV		8	12	pF

<sup>\*</sup> This parameter is periodically sampled and is not 100% tested.

### **TIMING WAVEFORMS (READ)**



## HIGH SPEED PROGRAM OPERATION

## D. C. RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN. T	TYP.	MAX.	UNIT
Vін	Input High Voltage	2.0		V <sub>CC</sub> +1.0	V
VIII.	input Low Voltage	-0.3		0.8	
Vcc	Vcc Power Supply Voltage	5.75	6.00	6.25	V -
VPP	VPP Power Supply Voltage	12.0	12.5	13.0	^ ·- · -

## **D. C. and OPERATING CHARACTERISTICS** (Ta = $25\pm5$ C, $V_{CC}$ – $6V\pm0.25V$ , $V_{PC}$ – $12.5V\pm0.5V$ )

SYMBOL	PARAMETER	TEST CONDITION	MIN. TYP	TMAX UNIT
1 10	Input Current	V <sub>IN</sub> =O~V <sub>CC</sub>		+10 µA
Voн	Output High Voltage	Іон ≕ − 400μА	2.4	
Voi	Output Low Voltage	IoL = 2.1mA		To.4   V 1
lcc .	Vcc Supply Current			120 mA
I IPP2	V <sub>PP</sub> Supply Current	V <sub>PP</sub> = 13.0V		†50 † mA

## A. C. PROGRAMMING CHARACTERISTICS (Ta= $25\pm5$ °C, $V_{CC}=6V\pm0.25V$ , $V_{PP}=12.5V\pm0.5V$ )

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
tas	Address Setup Time		2		†	μS
tantan	Address Hold Time	_	2			μS
tors	CE Setup Time		2			μS
torn	CE Hold Time	_	2			μS
tos	Data Setup Time		2	·	†	μS
ton	Data Hold Time		2	_		μS
tvs	V <sub>PP</sub> Setup Time	_	2			, μS
tew	Initial Program Pulse Width		0.95	1.0	1.05	/: ms
topw	Additional Program Pulse Width	Note 1	2.85		78.75	ms
teri	Program Pulse Rise Time		5			ns
teri	Program Pulse Fall Time		5		tt	ns
toe	OE to Output Valid			_	100	ns
tor2	OE to Output in High Z	CE = VII			90	ns

## A. C. TEST CONDITIONS

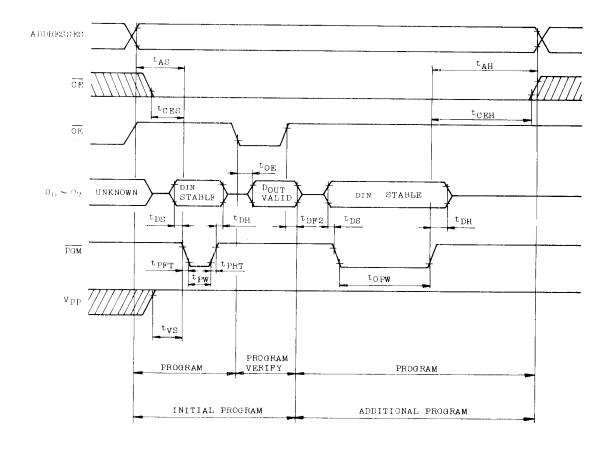
• Output Load : 1 TTL Gate and C<sub>L</sub>(100pF)

Input Pulse Rise and Fall Time
 Input Pulse Levels
 ∴ 10ns Max.
 ∴ 0.45 to 2.4V

• Timing Measurement Reference Level : Input 0.8V and 2.0V: Output 0.8V and 2.0V

Note: 1. t<sub>OPW</sub> depends on the program pulse width which is required in the initial Program.

## TIMING WAVEFORMS (HIGH SPEED PROGRAM)



Note: 1. Vcc must be applied simultaneously or before VPP and cut off simultaneously or after VPP.

 Removing the device from socket and setting the device in socket with V<sub>PP</sub>=12.5V may cause permanent damage to the device.

The V<sub>PP</sub> supply voltage is permitted up to 14V for program operation, so the voltage over 14V should not be applied to the V<sub>PP</sub> terminal.

When the switching pulse voltage is applied to the  $V_{PP}$  terminal, the overshoot voltage of its pulse should not be exceeded 14V.

## **ERASURE CHARACTERISTICS**

The TMM2764AD's erasure is achieved by applying shortwave ultraviolet light which has a wavelength of 2537A (Angstroms) to the chip through the transparent window.

Then integrated dose (ultraviolet light intensity [w/cm²] × exposure time [sec.] ) for erasure should be a minimum of 15 [W. sec/cm²]

When the Toshiba sterilizing lamp GL-15 is used and the device is exposed at a distance of 1cm from the lamp surface, the erasure will be achieved within 60 minutes.

And using commercial lamps whose ultraviolet

light intensity is a 12000  $[\mu w/cm^2]$  will reduce the exposure time to about 20 minutes. (In this case, the integrated does is 12000  $[\mu w/cm^2] \times (20 \times 60)$  [sec]  $\approx$  15  $[w \cdot sec/cm^2]$ .)

The TMM2764AD's erasure begins to occur when exposed to light with wavelength shorter than 4000Å. The sunlight and the flourescent lamps will include 3000~4000Å wavelength components. Therefore when used under such lighting for extended periods of time, the opaque seals-Toshiba EPROM Protect Seal AC901-are available.

#### **OPERATION INFORMATION**

The TMM2764AD's six operation modes are listed in the following table.

Mode selection can be achieved by applying TTL level signal to all inputs.

In the read operation mode, a single 5V power supply is required and the levels required for all inputs are TTL.

***************************************		PGM (27)	CE (20)	OE (22)	V <sub>PP</sub> (1)	V <sub>CC</sub> (28)	0 <sub>0</sub> ~0 <sub>7</sub> (11~13, 15~19)	POWER	
READ	Read	H	L	L			Data Out	Active	
OPERATION	Output Deselect	*	*	Н	5V 5V		High Impedance	Active	
(Ta = 0 ~ 70°C)	Standby	*	Н	*			High Impedance	Standby	
PROGRAM OPERATION (Ta=25±5°C)	Program	L	L	*			Data In	Active	
	Program Inhibit	*	Н	*	12.5V 6V	617	High Impedance	Active	
		Н	L	Н		ΟV	High Impedance	Active	
	Program Verify	Н	L	L	1		Data Out	Active	

Note  $H:V_{II}$ ,  $L:V_{IL}$ , \* :  $V_{IH}$  or  $V_{IL}$ 

#### **READ MODE**

The TMM2764AD has three control functions. The chip enable  $(\overline{CE})$  controls the operation power and should be used for device selection.

The output enable  $(\overline{OE})$  and the program control  $(\overline{PGM})$  control the output buffers, independent of device selection.

Assuming that  $\overrightarrow{CE} = \overrightarrow{OE} = V_{IL}$  and  $\overrightarrow{PGM} = V_{IH}$ , the output data is valid at the outputs after address access time from stabilizing of all addresses.

#### **OUTPUT DESELECT MODE**

Assuming that  $\overrightarrow{CE} = V_{IH}$  or  $\overrightarrow{OE} = V_{IH}$ , the outputs will be in a high impedance state.

So two or more TMM2764AD can be connected

The  $\overline{\text{CE}}$  to output valid (tce) is equal to the address access time (tacc).

Assuming that  $\overline{CE}=V_{IL}$ ,  $\overline{PGM}=V_{IH}$  and all addresses are valid, the output data is valid at the outputs after toe from the falling edge of  $\overline{OE}$ .

And assuming that  $\overline{CE} = \overline{OE} = V_{IL}$  and all addresses are valid, the output data is valid at the outputs after team from the rising edge of  $\overline{PGM}$ .

together on a common bus line.

When  $\overline{\text{CE}}$  is decoded for device selection, all deselected devices are in low power standby mode.

#### STANDBY MODE

The TMM2764AD has a low power standby mode controlled by the CE signal.

By applying a TTL high level to the CE input, the TMM2764AD is placed in the standby mode which

reduce 70% of the operating current and then the outputs are in a high impedance state, independent of the OE and the PGM inputs.

#### **PROGRAM MODE**

Initially, when received by customers, all bits of the TMM2764AD are in the "1" state which is erased state.

Therefore the program operation is to introduce "Os" data into the desired bit locations by electrically

#### **PROGRAM VERIFY MODE**

The verify mode is to check that the desired data is correctly programmed on the programmed bits.

#### **PROGRAM INHIBIT MODE**

Under the condition that the program voltage (+12.5V) is applied to  $V_{PP}$  terminal, a high level  $\overline{CE}$  or  $\overline{PGM}$  input inhibits the TMM2764AD from being programmed.

Programming of two or more TMM2764AD's in parallel with different data is easily accomplished.

#### HIGH SPEED PROGRAMMING MODE

The program time can be greatly decreased by using this high speed programming mode.

The device is set up in the high speed programming mode when the programming voltage( $\pm 12.5V$ ) is applied to the V<sub>PP</sub> terminal with V<sub>CC</sub>=6V and PGM = V<sub>IH</sub>.

The programming is achieved by applying a single TTL low level 1ms pulse the PGM input after addresses and data are stable. Then the programmed data is verified by using Program Verify Mode.

If the programmed data is not correct, another

programming.

The levels required for all inputs are TTL.

The TMM2764AD can be programmed any location at anytime—either individually, sequentially, or at random.

The verify is accomplished with  $\overline{OE}$  and  $\overline{CE}$  at V<sub>IL</sub> and  $\overline{PGM}$  at V<sub>IH</sub>.

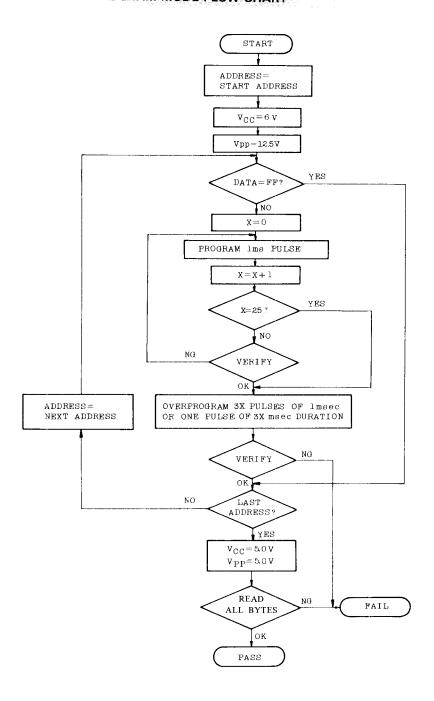
That is, all inputs except for  $\overline{CE}$  or  $\overline{PGM}$  may be commonly connected, and a  $\overline{TL}$  low level program pulse is applied to the  $\overline{CE}$  and  $\overline{PGM}$  of the desired device only and  $\overline{TL}$  high level signal is applied to the other devices.

program pulse of 1rns is applied and then programmed data is verified. This should be repeated until the program operates correctly (max.25 times)

After correctly programming the selected address, one additional program pulse with pulse width 3 times that needed for programming is applied.

When programming has been completed, the data in all addresses should be verified with  $V_{CC} = V_{PP} = 5V$ .

## HIGH SPEED PROGRAM MODE FLOW CHART



## **ELECTRIC SIGNATURE MODE**

Electric signature mode allows to read out a code from TMM2764AD which identifies its manufacture and device type.

The programming equipment may read out manufacturer code and device code from TMM2764AD by using this mode before program operation and automatically set program voltage (VPP) and algorithm.

Electric signature mode is set up when 12V is

applied to address line A9 and the rest of address lines is set to  $V_{\rm IL}$  in read operation. Data output in this conditions is manufacturer code. Device code is identified when address AO is set to  $V_{\rm IH}$ . These two codes possess an ocd parity with the parity bit of MSB (07).

The following table shows electric signature of TMM2764AD.

PINS SIGNATURE	A <sub>0</sub> (10)	O <sub>7</sub> (19)	O <sub>6</sub> (18)	O <sub>5</sub> (17)	O <sub>4</sub> (16)	O <sub>3</sub> (15)	O <sub>2</sub> (13)	O <sub>1</sub> (12)	O <sub>0</sub> (11)	HEX. DATA
Manufacture Code	VII	1	0	0	1	1	0	0	0	98
Device Code	VIII	0	1	0	1	0	0	1	0	52

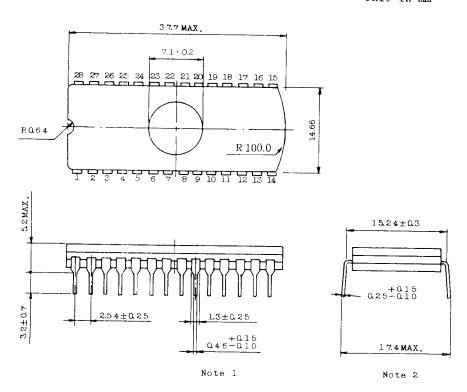
Notes:  $A9 = 12V \pm 0.5V$ 

 $\underline{A1} \sim A8$ ,  $\underline{A10} \sim A12$ ,  $\overline{CE}$ ,  $\overline{OE} = V_{1L}$ 

PGM=V<sub>IH</sub>

#### **OUTLINE DRAWINGS**

Unit in mm



Note: 1. Each lead pitch is 2.54mm. All leads are located within 0.25mm of their true longitudinal position with respect No.1 and No.28 eads.

- 2. This value is measured at the end of leads.
- 3. All dimensions are in millimeters.

Note: Toshiba does not assume any responsibility for use of any circuitry described , no circuit patent licenses are implied, and Toshiba reserves the right, at any time without notice, to change said circuitry.

\*C'May., 1986 Toshiba Corporation